



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

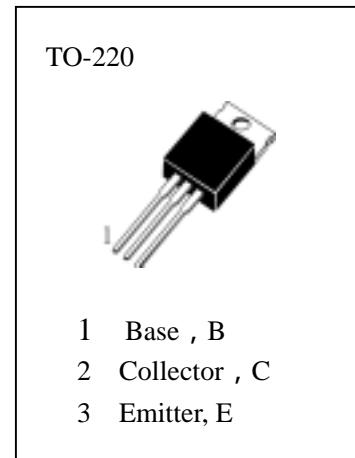
**HE2955**

## GENERAL PURPOSE AND SWITCHING APPLICATIONS

### DCCURRENT GAIN SPECIFIED TO 10 AMPERES

#### ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$	Storage Temperature.....	-55~150
$T_j$	Junction Temperature.....	150
$P_C$	Collector Dissipation( $T_c=25^\circ C$ ).....	-75W
$P_C$	Collector Dissipation( $T_A=25^\circ C$ ).....	0.6W
$V_{CBO}$	Collector-Base Voltage.....	-70V
$V_{CEO}$	Collector-Emitter Voltage.....	-60V
$V_{EBO}$	Emitter-Base Voltage.....	-5V
$I_C$	Collector Current( DC ).....	-10A
$I_B$	Base Current.....	-6A



#### 电参数 ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CEO}$	Collector-Emitter Sustaining Voltage	-60			V	$I_C=-10mA, I_B=0$
$I_{CEO}$	Collector Cutoff Current			-0.7	mA	$V_{CE}=-30V, I_B=0$
$I_{EBO}$	Emitter-Base Cutoff Current			-5	mA	$V_{EB}=-5V, I_C=0$
$HFE (1)$	DC Current Gain	20		100		$V_{CE}=-4V, I_C=-4A$
$HFE (2)$		5				$V_{CE}=-4V, I_C=-10A$
$V_{CE(sat1)}$	Collector- Emitter Saturation Voltage			-1.1	V	$I_C=-4A, I_B=-400mA$
$V_{CE(sat2)}$				-8	V	$I_C=-10A, I_B=-3.3mA$
$V_{BE(on)}$	Base- Emitter Saturation Voltage			-1.8	V	$V_{CE}=-4V, I_C=-4A$
$f_T$	Current Gain-Bandwidth Product	2.0				$V_{CE}=-10V, I_C=-500mA$ $f=500KHz$